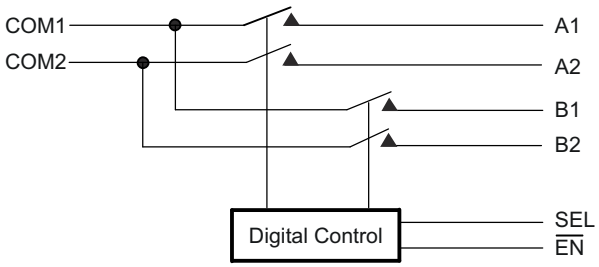
TMUX136 具有断电隔离功能的 6GHz 双通道 2:1 开关

1 特性

- V_{CC} 范围 2.3V 至 4.8V
- 高性能开关特性：
  - 带宽（–3dB）：6.1GHz
  - R_{ON}（典型值）：5.7Ω
  - C_{ON}（典型值）：1.6pF
- 电流消耗：30μA（典型值）
- 专有特性：
  - I_{OFF} 保护可防止在断电状态下产生漏电流
  - 1.8V 兼容控制输入（SEL，$\overline{EN}$）
- 直通引脚排列可简化 PCB 布局
- 与高速 I^3C 信号兼容
- ESD 性能：
  - 5kV 人体放电模型（A114B，II 类）
  - 1kV 充电器件模型 (C101)
- 紧凑型 10 引脚 UQFN 封装（1.5mm × 2mm，间距为 0.5mm）

2 应用

- I^3C (SenseWire)
- 移动行业处理器接口 (MIPI)
- 服务器
- 手持终端：智能手机
- 笔记本电脑
- 平板电脑：多媒体
- 电子销售终端
- 现场仪器
- 便携式监视器



简化原理图

3 说明

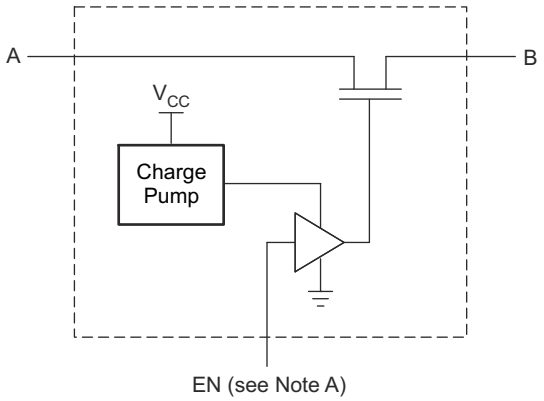
TMUX136 器件是一款高性能 6GHz 双通道 2:1 开关，同时支持差分和单端信号。该器件具有 2.3V 至 4.8V 的较宽 V_{CC} 范围，支持断电保护功能，当 V_{CC} 引脚断电时，强制所有 I/O 引脚进入高阻抗模式。TMUX136 的部分引脚支持 1.8V 控制电压，允许它们直接与低电压处理器的通用 I/O (GPIO) 相连。输入和输出分别位于器件两侧的直通引脚排列简化了布局布线。这一特性连同器件的低导通电阻和低导通电容，使得 TMUX136 成为支持切换各种模拟信号和数字通信协议标准（包括 I^3C 等高速标准）的出色器件。

TMUX136 采用小型 10 引脚 UQFN 封装，尺寸仅为 1.5mm × 2mm，非常适合 PCB 面积有限的情况。

封装信息

器件型号	封装(1)	封装尺寸(2)
TMUX136	RSE（UQFN，10）	2mm × 1.5mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。
(2) 封装尺寸（长 × 宽）为标称值，并包括引脚（如适用）。



Note A: EN is the internal enable signal applied to the switch.

功能方框图

Table of Contents

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision D (August 2020) to Revision E (June 2023)	Page
• 向数据表添加了 *I³C (SenseWire)* 应用信息	1
• 添加了*封装信息* 表	1

Changes from Revision C (July 2018) to Revision D (August 2020)	Page
• Added new specification limits to support added temperature range T_A = *-40°C to +125°C*	4

Changes from Revision B (November 2017) to Revision C (July 2018)	Page
• Changed pin 6 To: $\overline{EN}$, pin 7 To: COM2, and pin 8 To: COM1 in 图 9-19	17

Changes from Revision A (October 2017) to Revision B (November 2017)	Page
• Changed Pin 7 From: COM1 To: COM2	3
• Changed Pin 8 From: COM2 To: COM1	3

Changes from Revision * (August 2017) to Revision A (October 2017)	Page
• Changed the HBM value From: ±3500 To: ±5000 in the *ESD Ratings* table	4

5 Pin Configuration and Functions

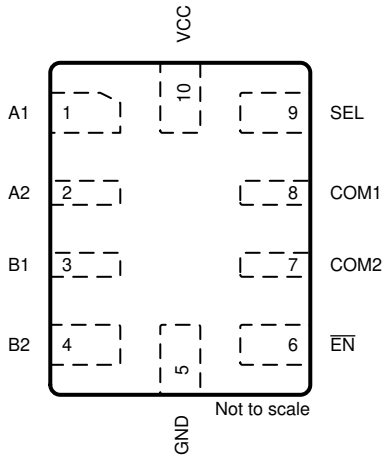


图 5-1. RSE Package, 10-Pin UQFN (Top View)

表 5-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NO.	NAME		
1	A1	I/O	Signal path A1
2	A2	I/O	Signal path A2
3	B1	I/O	Signal path B1
4	B2	I/O	Signal path B2
5	GND	—	Ground
6	$\overline{EN}$	I	Enable (active low)
7	COM2	I/O	Common signal path 2
8	COM1	I/O	Common signal path 1
9	SEL	I	Switch select (logic Low = COM to A PORT Logic High = COM to B PORT)
10	V_{CC}	—	Supply voltage

(1) I = input, O = output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(3)		– 0.3	5.5	V
$V_{I/O}$	Input-output DC voltage(3)		– 0.3	5.5	V
V_{SEL}, $V_{\overline{EN}}$	Digital input voltage (SEL, $\overline{EN}$)		– 0.3	5.5	V
I_K	Input-output port diode current	VI/O < 0	– 50		mA
I_{IK}	Digital logic input clamp current(3)	VI < 0	– 50		mA
I_{CC}	Continuous current through V_{CC}			100	mA
I_{GND}	Continuous current through GND		– 100		mA
T_{stg}	Storage temperature		– 65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(3) All voltages are with respect to ground, unless otherwise specified.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±5000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V_{CC}	Supply voltage	2.3	4.8	V
$V_{I/O}$	Analog voltage	0	3.6	V
V_{SEL}, $V_{\overline{EN}}$	Digital input voltage (SEL, $\overline{EN}$)	0	V_{CC}	V
T_{RAMP} (V_{CC})	Power supply ramp time requirement (V_{CC})	100	1000	μs/V
$I_{I/O}$	Continuous current through I/O signal path (COMx, Ax, Bx) T_A = – 40°C to +85°C		±20	mA
$I_{I/O}$	Continuous current through I/O signal path (COMx, Ax, Bx) T_A = – 40°C to +125°C		±10	mA
T_A	Operating free-air temperature	– 40	125	°C

6.4 Thermal Information

THERMAL METRIC (1)		TMUX136 RSE (UQFN) 10 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	191.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	94.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	117.5	°C/W
ψ_{JT}	Junction-to-top characterization parameter	7.4	°C/W
ψ_{JB}	Junction-to-board characterization parameter	117.4	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

T_A = –40°C to +85°C, Typical values are at V_{CC} = 3.3 V, T_A = 25°C, (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
A PORT SWITCH							
R_{ON}	ON-state resistance	V_{CC} = 2.7 V	$V_{I/O}$ = 1.65 V, I_{ON} = –8 mA		5.7	9	Ω
		V_{CC} = 2.3 V	$V_{I/O}$ = 1.65 V, I_{ON} = –8 mA		5.7	9.5	
		V_{CC} = 2.7 V	$V_{I/O}$ = 1.65 V, I_{ON} = –8 mA T_A = –40°C to +125°C			13	
		V_{CC} = 2.3 V	$V_{I/O}$ = 1.65 V, I_{ON} = –8 mA T_A = –40°C to +125°C			13	
ΔR_{ON}	ON-state resistance match between signal path 1 and 2	V_{CC} = 2.3 V	$V_{I/O}$ = 1.65 V, I_{ON} = –8 mA		0.1		Ω
$R_{ON(FLAT)}$	ON-state resistance flatness	V_{CC} = 2.3 V	$V_{I/O}$ = 1.65 V to 3.45 V, I_{ON} = –8 mA		1		Ω
I_{OZ}	OFF leakage current	V_{CC} = 4.8 V	Switch OFF, V_B = 1.65 V to 3.45 V, V_{COM} = 0 V	–2		2	µA
			Switch OFF, V_B = 1.65 V to 3.45 V, V_{COM} = 0 V T_A = –40°C to +125°C	–15		15	
I_{OFF}	Power-off leakage current	V_{CC} = 0 V	Switch ON or OFF, V_B = 1.65 V to 3.45 V, V_{COM} = NC	–10		10	µA
			Switch ON or OFF, V_B = 1.65 V to 3.45 V, V_{COM} = NC T_A = –40°C to +125°C	–50		50	
I_{ON}	ON leakage current	V_{CC} = 4.8 V	Switch ON, V_B = 1.65 V to 3.45 V, V_{COM} = NC	–2		2	µA
			Switch ON, V_B = 1.65 V to 3.45 V, V_{COM} = NC T_A = –40°C to +125°C	–15		15	
		V_{CC} = 2.3 V	Switch ON, V_B = 1.65 V to 3.45 V, V_{COM} = NC	–125		125	
			Switch ON, V_B = 1.65 V to 3.45 V, V_{COM} = NC T_A = –40°C to +125°C	–175		175	
B PORT SWITCH							
R_{ON}	ON-state resistance	V_{CC} = 2.3 V	$V_{I/O}$ = 0.4 V, I_{ON} = –8 mA		4.6	7.5	Ω
			$V_{I/O}$ = 0.4 V, I_{ON} = –8 mA T_A = –40°C to +125°C			12	

6.5 Electrical Characteristics (continued)

T_A = –40°C to +85°C, Typical values are at V_{CC} = 3.3 V, T_A = 25°C, (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ΔR_{ON}	ON-state resistance match between signal path 1 and 2	V_{CC} = 2.3 V	$V_{I/O}$ = 0.4 V, I_{ON} = –8 mA		0.1		Ω
$R_{ON(FLAT)}$	ON-state resistance flatness	V_{CC} = 2.3 V	$V_{I/O}$ = 0 V to 0.4 V, I_{ON} = –8 mA		1		Ω
I_{OZ}	OFF leakage current	V_{CC} = 4.8 V	Switch OFF, V_A = 0 V to 3.6 V, V_{COM} = 0 V	–2		2	µA
			Switch OFF, V_A = 0 V to 3.6 V, V_{COM} = 0 V T_A = –40°C to +125°C	–15		15	
I_{OFF}	Power-off leakage current	V_{CC} = 0 V	Switch ON or OFF, V_A = 0 V to 3.6 V, V_{COM} = NC	–10		10	µA
			Switch ON or OFF, V_A = 0 V to 3.6 V, V_{COM} = NC T_A = –40°C to +125°C	–50		50	
I_{ON}	ON leakage current	V_{CC} = 4.8 V	Switch ON, V_A = 0 V to 3.6 V, $V_{D±}$ = NC	–2		2	µA
		V_{CC} = 4.8 V	Switch ON, V_A = 0 V to 3.6 V, $V_{D±}$ = NC T_A = –40°C to +125°C	–15		15	
		V_{CC} = 2.3 V	Switch ON, V_A = 0 V to 3.6 V, V_B = NC	–125		125	
		V_{CC} = 2.3 V	Switch ON, V_A = 0 V to 3.6 V, V_B = NC T_A = –40°C to +125°C	–175		175	
DIGITAL CONTROL INPUTS (SEL, $\overline{EN}$)							
V_{IH}	Input logic high	V_{CC} = 2.3 V to 4.8 V T_A = –40°C to +125°C		1.3			V
V_{IL}	Input logic low	V_{CC} = 2.3 V to 4.8 V T_A = –40°C to +125°C				0.6	V
I_{IN}	Input leakage current	V_{CC} = 4.8 V, $V_{I/O}$ = 0 V to 3.6 V, V_{IN} = 0 to 4.8 V		–10		10	µA

6.6 Dynamic Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
C_{ON}	PORT B ON capacitance	V_{CC} = 3.3 V, $V_{I/O}$ = 0 or 3.3 V, f = 240 MHz	Switch ON		1.6	2	pF
	PORT A ON capacitance	V_{CC} = 3.3 V, $V_{I/O}$ = 0 or 3.3 V, f = 240 MHz	Switch ON		1.4	2	pF
C_{OFF}	PORT B OFF capacitance	V_{CC} = 3.3 V, $V_{I/O}$ = 0 or 3.3 V f = 240 MHz	Switch OFF		1.4	2	pF
	PORT A OFF capacitance	V_{CC} = 3.3 V, $V_{I/O}$ = 0 or 3.3 V f = 240 MHz	Switch OFF		1.6	2	pF
C_I	Digital input capacitance	V_{CC} = 3.3 V, V_I = 0 or 2 V			2.2		pF
O_{ISO}	OFF Isolation	V_{CC} = 2.3 V to 4.8 V, R_L = 50 Ω, f = 240 MHz	Switch OFF		– 34		dB
X_{TALK}	Crosstalk	V_{CC} = 2.3 V to 4.8 V, R_L = 50 Ω, f = 240 MHz	Switch ON		– 37		dB
BW	– 3-dB bandwidth	V_{CC} = 2.3 V to 4.8 V, R_L = 50 Ω,	Switch ON		6.1		GHz
SUPPLY							
V_{CC}	Power supply voltage			2.3		4.8	V
I_{CC}	Positive supply current	V_{CC} = 4.8 V, V_{IN} = V_{CC} or GND, $V_{I/O}$ = 0 V, Switch ON or OFF			30	50	μA
		V_{CC} = 4.8 V, V_{IN} = V_{CC} or GND, $V_{I/O}$ = 0 V, Switch ON or OFF T_A = – 40°C to +125°C				70	
$I_{cc, HZ}$	Power supply current in high-Z mode	V_{CC} = 4.8 V, V_{IN} = V_{CC} or GND, $V_{I/O}$ = 0 V, Switch ON or OFF, $\overline{OE}$ = H			5	10	μA
		V_{CC} = 4.8 V, V_{IN} = V_{CC} or GND, $V_{I/O}$ = 0 V, Switch ON or OFF, $\overline{OE}$ = H T_A = – 40°C to +125°C				20	

6.7 Timing Requirements

				MIN	NOM	MAX	UNIT
t_{pd}	Propagation delay		R_L = 50 Ω, C_L = 5 pF, V_{CC} = 2.3 V to 4.8 V		100		ps
t_{switch}	Switching time (SEL to output)					600	ns
$t_{ZH, ZL}$	Enable time ($\overline{EN}$ to output)	$V_{I/O}$ = 3.3 V or 0 V			100		μs
$t_{HZ, LZ}$	Disable time ($\overline{EN}$ to output)				200		ns
$t_{SK(P)}$	Skew of opposite transitions of same output				20		ps

6.8 Typical Characteristics

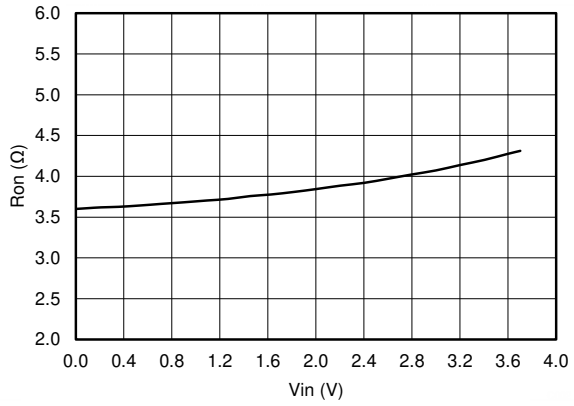


图 6-1. ON-Resistance vs $V_{I/O}$

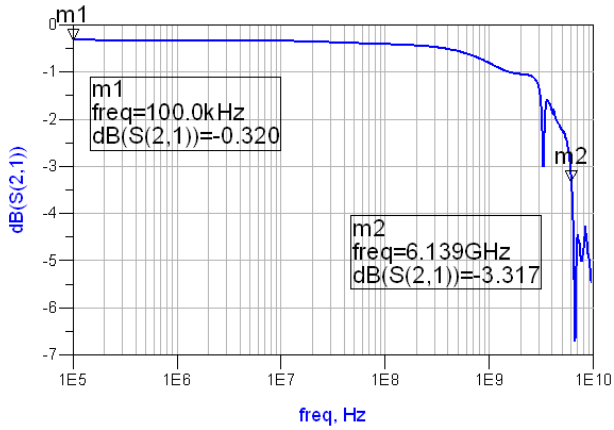


图 6-2. Bandwidth

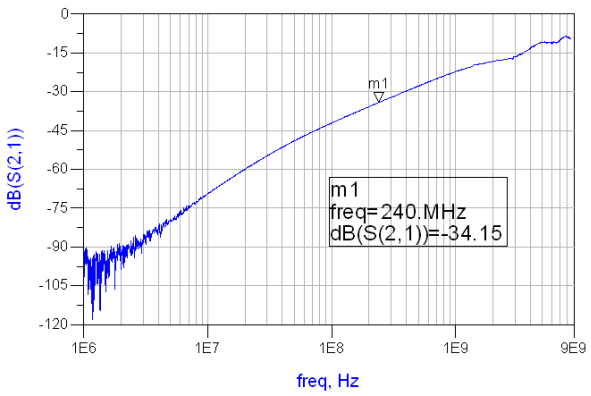


图 6-3. Off Isolation

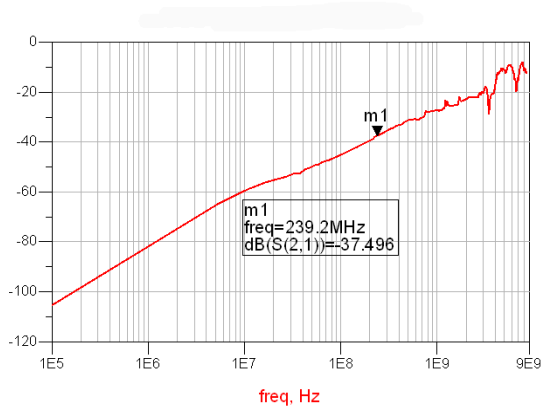
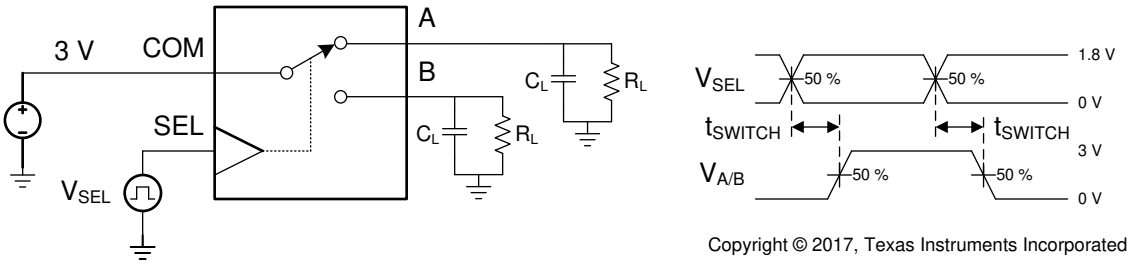


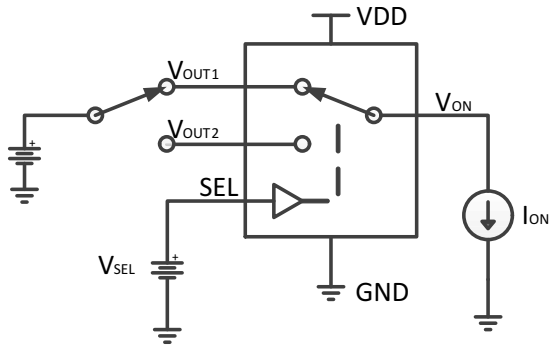
图 6-4. Cross Talk

7 Parameter Measurement Information



A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω , t_r < 5 ns, t_f < 5 ns.
B. C_L includes probe and jig capacitance.

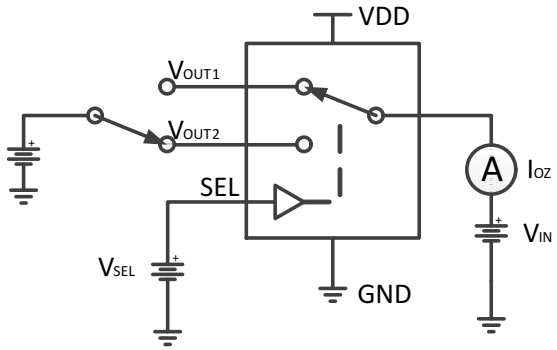
图 7-1. Timing Diagram



Channel ON

R_{ON} = (V_{ON} – $V_{I/O1}$) / I_{ON} or (V_{ON} – $V_{I/O2}$) / I_{ON}
V_{SEL} = H or L

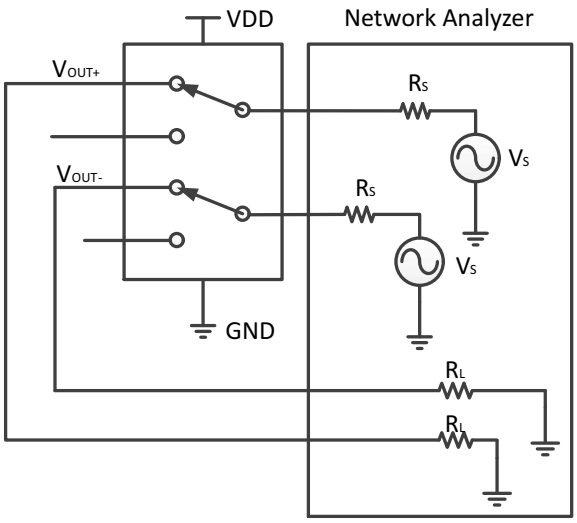
图 7-2. ON-State Resistance (R_{ON})



Channel OFF

V_{SEL} = H or L

图 7-3. OFF Leakage Current (I_{OZ})



Channel ON

V_{SEL} = H or L
R_S=R_L=50Ω

图 7-4. Bandwidth (BW)

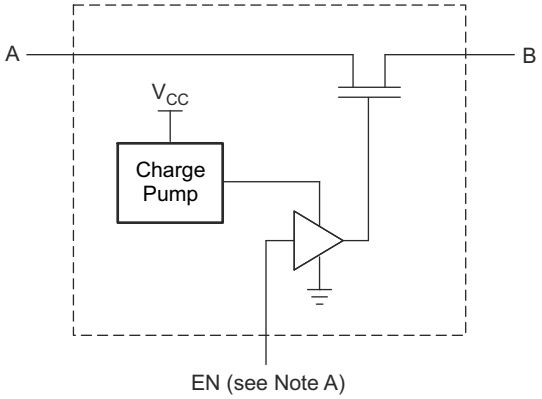
8 Detailed Description

8.1 Overview

The TMUX136 device is a 2-channel, 2:1, switch specifically designed for the switching of high-speed signals in handset and consumer applications, such as cell phones, tablets, and notebooks but may be used for any high speed application. The wide bandwidth (6.1 GHz) of this switch allows signals to pass with minimum edge and phase distortion. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs and will support both single-ended and differential signals. The device also has a low power mode that reduces the power consumption to 5 µA for portable applications with a battery or limited power budget.

The TMUX136 device integrates ESD protection cells on all pins, is available in a tiny UQFN package (1.5 mm × 2 mm) and is characterized over the free-air temperature range from –40°C to +125°C.

8.2 Functional Block Diagram



Note A: EN is the internal enable signal applied to the switch.

8.3 Feature Description

8.3.1 Low Power Mode

The TMUX136 has a low power mode that reduces the power consumption to 5 µA while the device is not in use. To put the device in low power mode and disable the switch, the bus-switch enable pin $\overline{EN}$ must be supplied with a logic High signal.

8.4 Device Functional Modes

8.4.1 High Impedance Mode

The TMUX136 has a high impedance mode that places all the signal paths in a Hi-Z state while the device is not in use. As provided in 表 8-1, to put the device in high impedance mode and disable the switch, the bus-switch enable pin $\overline{EN}$ must be supplied with a logic *High* signal.

表 8-1. Function Table

SEL	$\overline{EN}$	SWITCH STATUS
X	High	Both A PORT and B PORT switches in High-Z
Low	Low	COM to A PORT
High	Low	COM to B PORT

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

There are many applications in which microprocessors or controllers have a limited number of I/Os. The TMUX136 solution can effectively expand the limited I/Os by switching between multiple buses to interface them to a single microprocessor or controller. A common application where the TMUX136 is as a I3C 1:2 multiplexer. In this application, the TMUX136 is used to route communicating between different DDR modules from a single controller within a server, as shown in 图 9-1. The high bandwidth of the TMUX136 will preserve signal integrity at even the fastest communication protocols that may be used in server applications, such as I^3C.

9.2 Typical Application

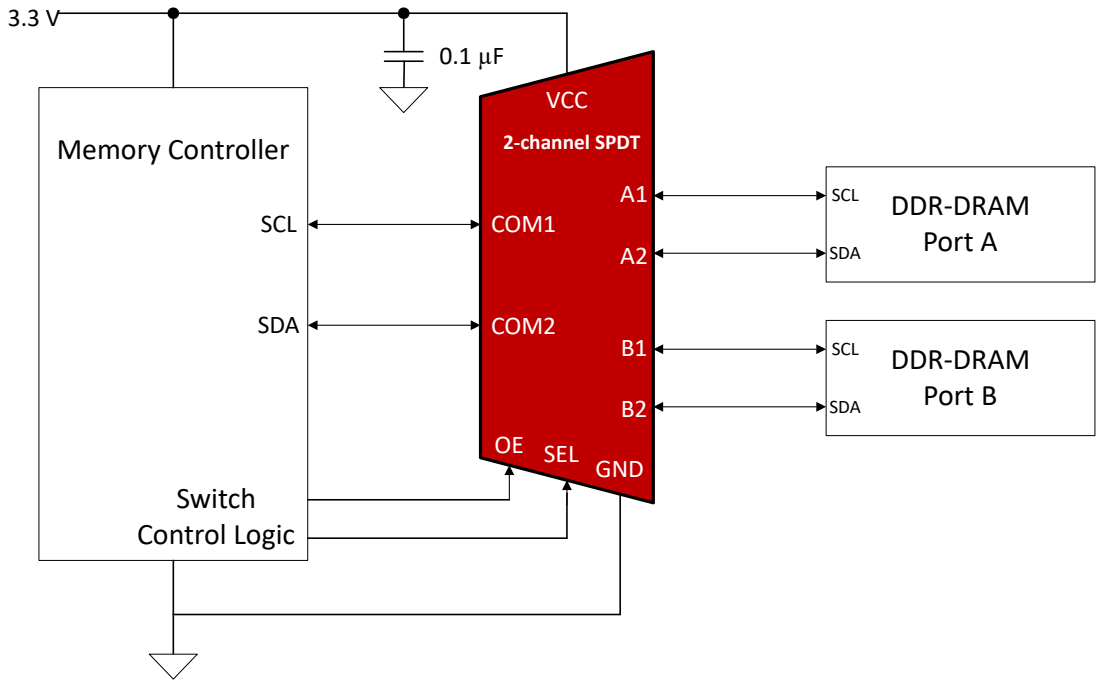


图 9-1. Typical Application

The TMUX136 supports I^3C standard by maintaining signal integrity through the switch. 表 9-1 details how the TMUX136 specifications make this device optimal for switching I^3C signals.

表 9-1. TMUX136 I^3C Compatibility

	I^3C Requirements	TMUX136 Specification
Voltage (I/O)	1.0 V, 1.2 V, 1.8 V, 3.3 V	0-3.6 V
Frequency	Up to 12.5 MHz	6 GHz Bandwidth
Capacitance	50 pF maximum bus capacitance	<2 pF On/Off Capacitance

9.2.1 Design Requirements

The TMUX136 has internal 6-MΩ pull-down resistors on SEL and $\overline{EN}$, so no external resistors are required on the logic pins. The internal pull-down resistor on SEL allows the PORT A channel to be selected by default. The internal pull-down resistor on $\overline{EN}$ enables the switch when power is applied to V_{CC}.

9.2.2 Detailed Design Procedure

The TMUX136 can operate without any external components; however, TI recommends that unused pins must be connected to ground through a 50-Ω resistor to prevent signal reflections back into the device.

9.2.3 Application Curves

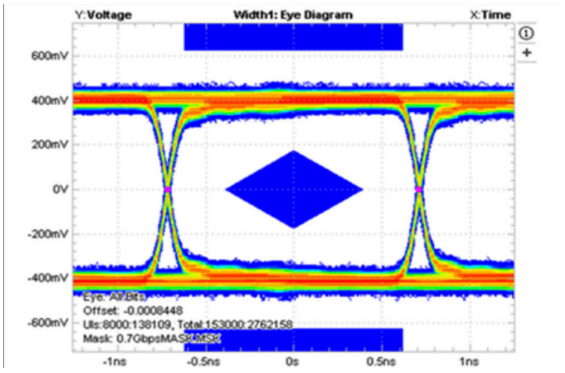


图 9-2. Eye Pattern: 0.7 Gbps with No Device

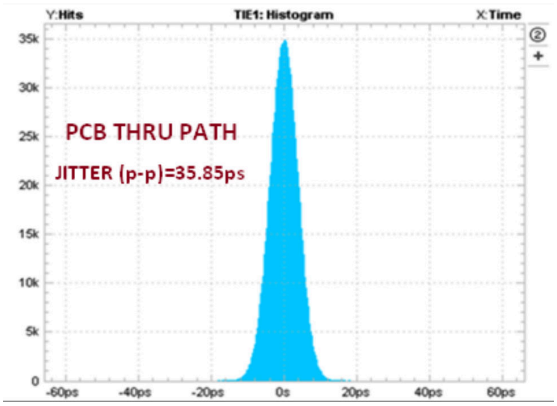
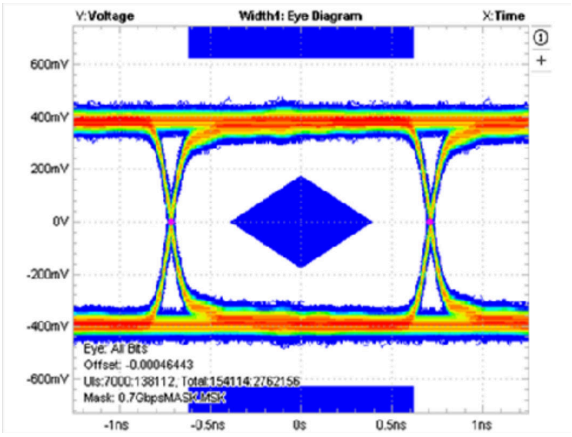
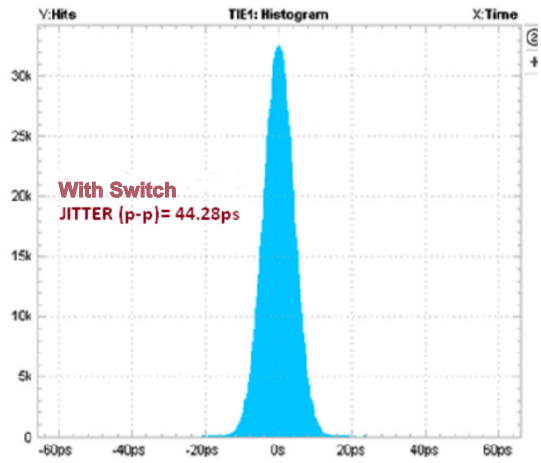


图 9-3. Time Interval Error Histogram: 0.7 Gbps with No Device



The TMUX136 contributes only 8.4 ps of peak-to-peak jitter for 0.7-Gbps data rate

图 9-4. Eye Pattern: 0.7 Gbps with Switch



The TMUX136 contributes only 8.4 ps of peak-to-peak jitter for 0.7-Gbps data rate

图 9-5. Time Interval Error Histogram: 0.7 Gbps with Switch

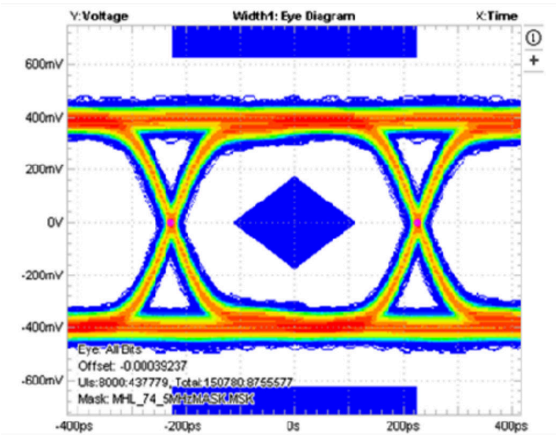


图 9-6. Eye Pattern: 2.2 Gbps with No Device

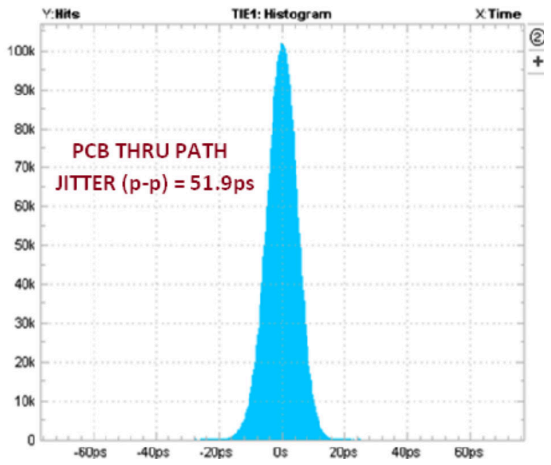
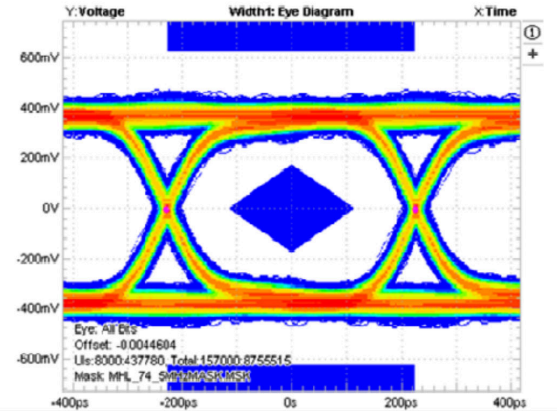
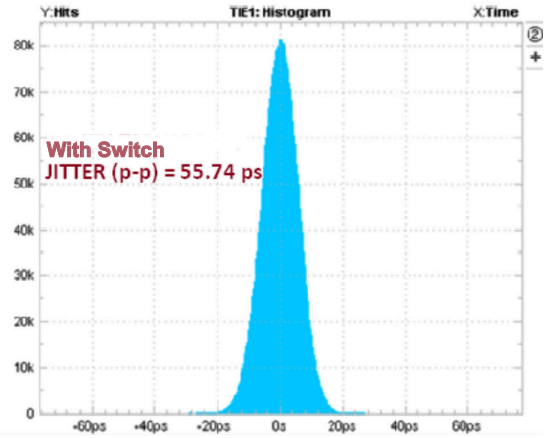


图 9-7. Time Interval Error Histogram: 2.2 Gbps with No Device



The TMUX136 contributes only 3.8 ps of peak-to-peak jitter for 2.2-Gbps data rate

图 9-8. Eye Pattern: 2.2 Gbps with Switch



The TMUX136 contributes only 3.8 ps of peak-to-peak jitter for 2.2-Gbps data rate

图 9-9. Time Interval Error Histogram: 2.2 Gbps with Switch

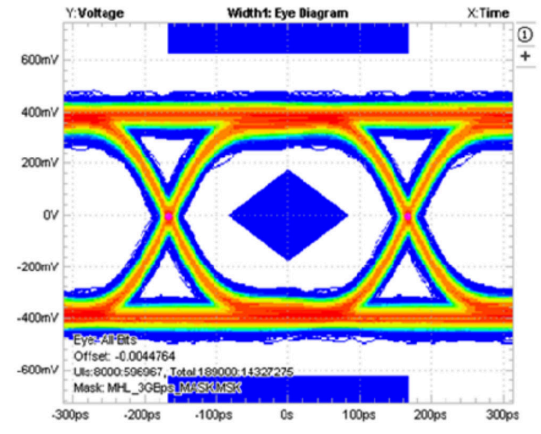


图 9-10. Eye Pattern: 3 Gbps with No Device

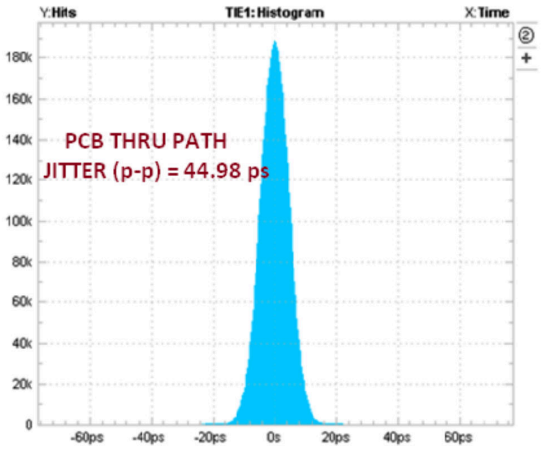
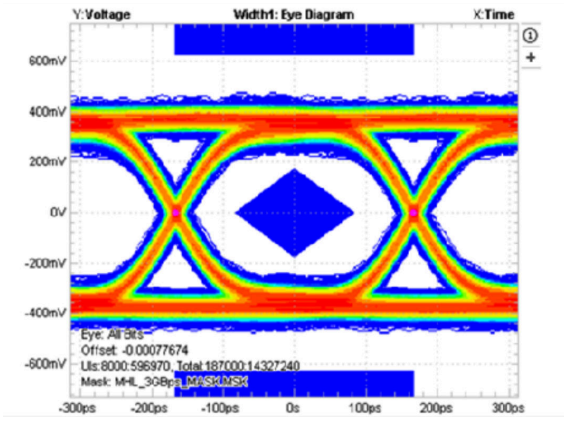
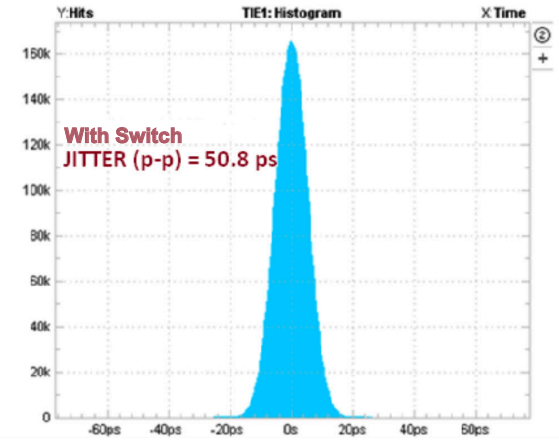


图 9-11. Time Interval Error Histogram: 3 Gbps with No Device



The TMUX136 contributes only 5.8 ps of peak-to-peak jitter for 3-Gbps data rate

图 9-12. Eye Pattern: 3 Gbps with Switch



The TMUX136 contributes only 5.8 ps of peak-to-peak jitter for 3-Gbps data rate

图 9-13. Time Interval Error Histogram: 3 Gbps with Switch

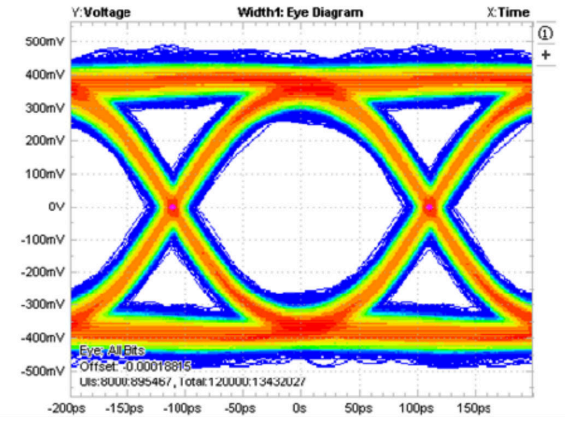


图 9-14. Eye Pattern: 4.5 Gbps with No Device

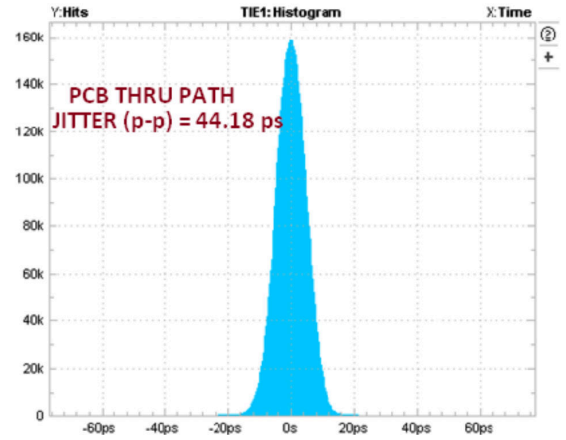
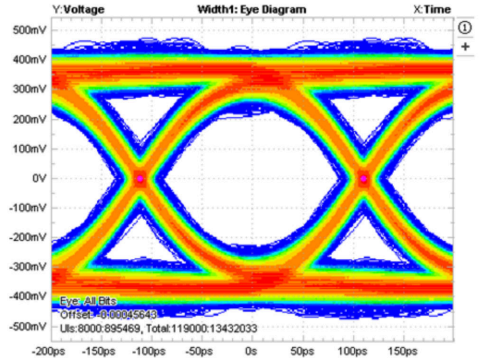
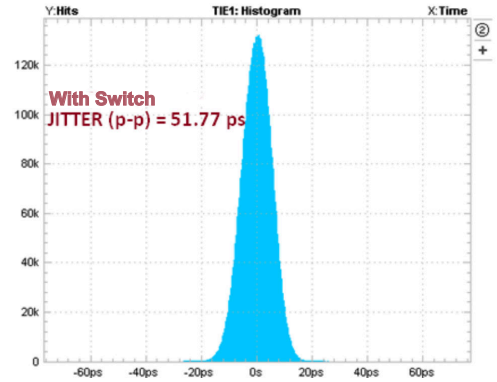


图 9-15. Time Interval Error Histogram: 4.5 Gbps with No Device



The TMUX136 contributes only 7.6 ps of peak-to-peak jitter for 4.5-Gbps data rate

图 9-16. Eye Pattern: 4.5 Gbps with Switch



The TMUX136 contributes only 7.6 ps of peak-to-peak jitter for 4.5-Gbps data rate

图 9-17. Time Interval Error Histogram: 4.5 Gbps with Switch

9.3 Power Supply Recommendations

TI recommends placing a bypass capacitor as close to the supply pin V_{CC} as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

9.4 Layout

9.4.1 Layout Guidelines

Place supply bypass capacitors as close to V_{CC} pin as possible and avoid placing the bypass capacitors near the high speed traces.

The high-speed signal paths must should be no more than 4 inches long; otherwise, the eye diagram performance may be degraded.

Route the high-speed signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal’s transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.

When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.

Do not route high speed signal traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices or ICs that use or duplicate clock signals.

Avoid stubs on the high-speed signals traces because they cause signal reflections. If a stub is unavoidable, then the stub must be less than 200 mm.

Route all high-speed signal traces over continuous GND planes, with no interruptions.

Avoid crossing over anti-etch, commonly found with plane splits.

Due to high frequencies, a printed circuit board with at least four layers is recommended; two signal layers separated by a ground and power layer as shown in 图 9-18.

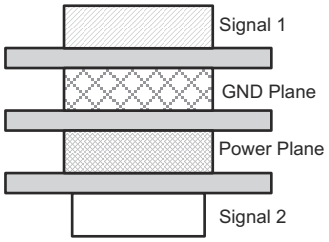


图 9-18. Four-Layer Board Stack-Up

The majority of signal traces must run on a single layer, preferably Signal 1. Immediately next to this layer must be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies.

9.4.2 Layout Example

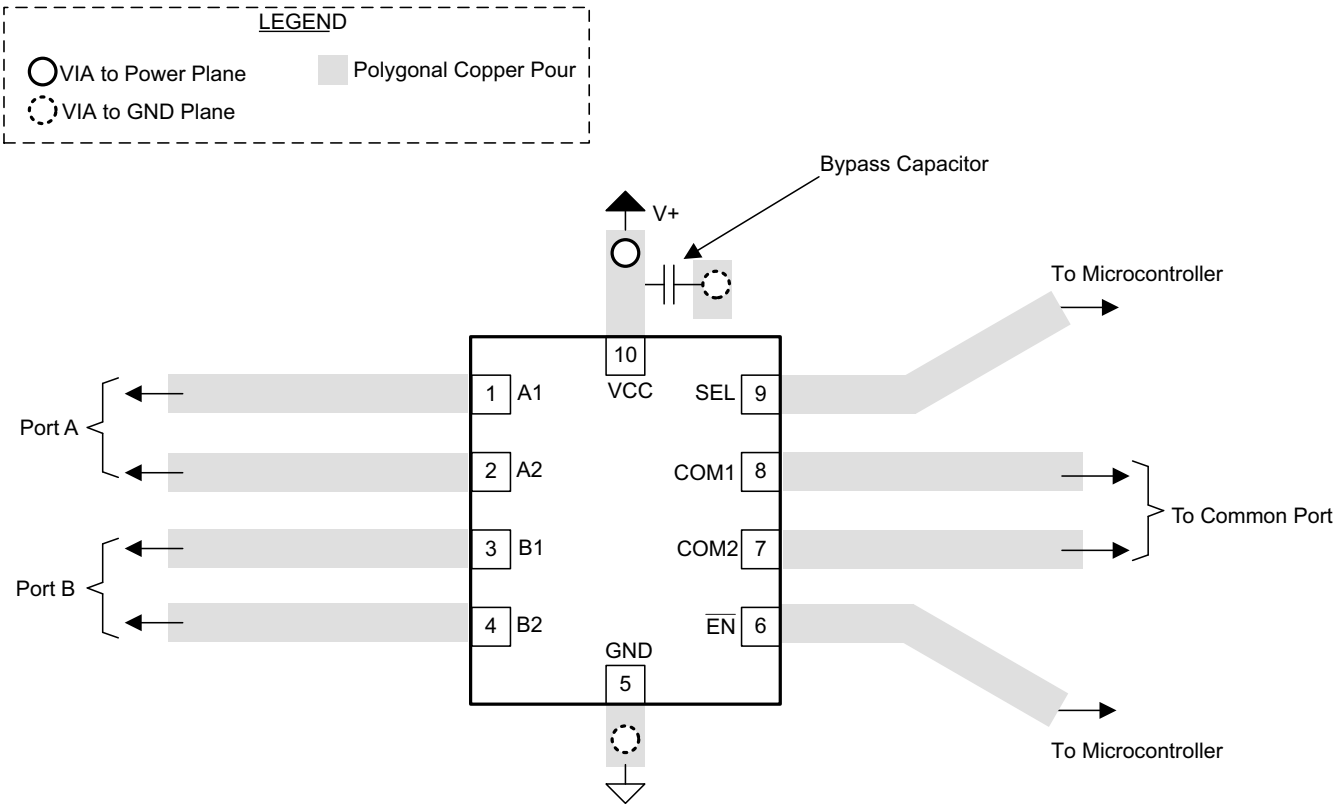


图 9-19. Package Layout Diagram

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *High-Speed Layout Guidelines Application Report*
- Texas Instruments, *High-Speed Interface Layout Guidelines*

10.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

10.4 Trademarks

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10.5 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

10.6 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TMUX136MRSER	Active	Production	UQFN (RSE) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	19H
TMUX136MRSER.A	Active	Production	UQFN (RSE) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	19H
TMUX136MRSERG4.A	Active	Production	UQFN (RSE) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	19H
TMUX136RSER	Active	Production	UQFN (RSE) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	19G
TMUX136RSER.A	Active	Production	UQFN (RSE) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	19G
TMUX136RSERG4.A	Active	Production	UQFN (RSE) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	19G

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

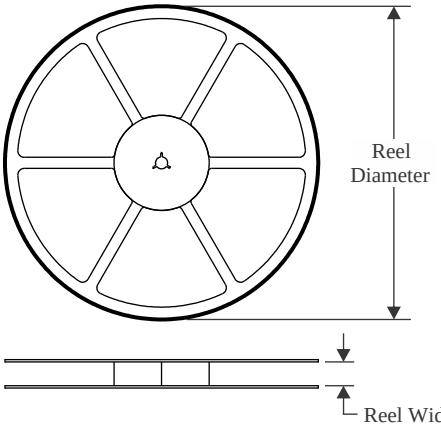
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

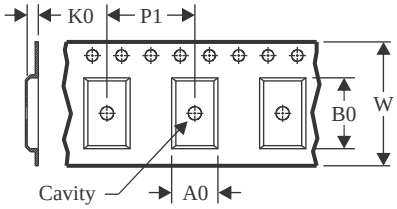
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

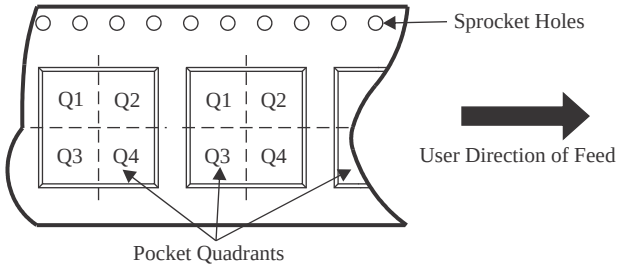


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

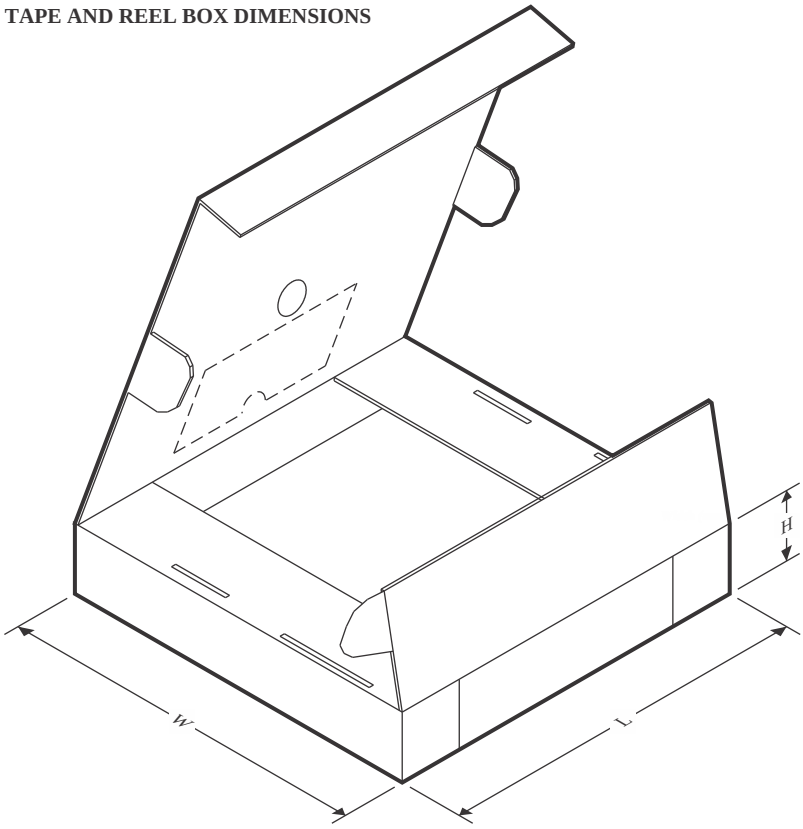
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMUX136MRSER	UQFN	RSE	10	3000	180.0	9.5	2.2	1.8	0.75	4.0	8.0	Q3
TMUX136RSER	UQFN	RSE	10	3000	180.0	9.5	1.7	2.2	0.75	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

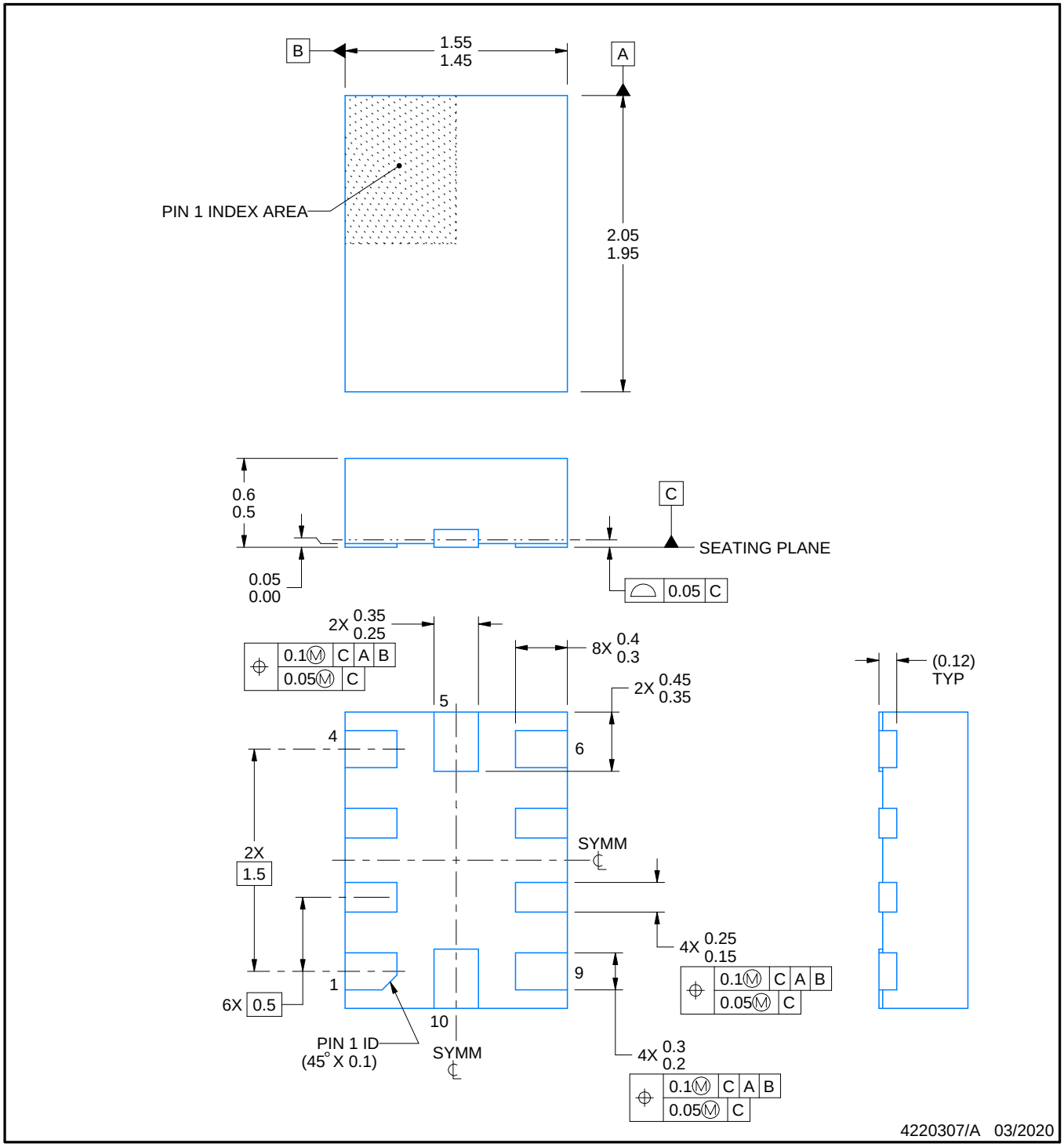
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMUX136MRSER	UQFN	RSE	10	3000	189.0	185.0	36.0
TMUX136RSER	UQFN	RSE	10	3000	189.0	185.0	36.0

RSE0010A

PACKAGE OUTLINE

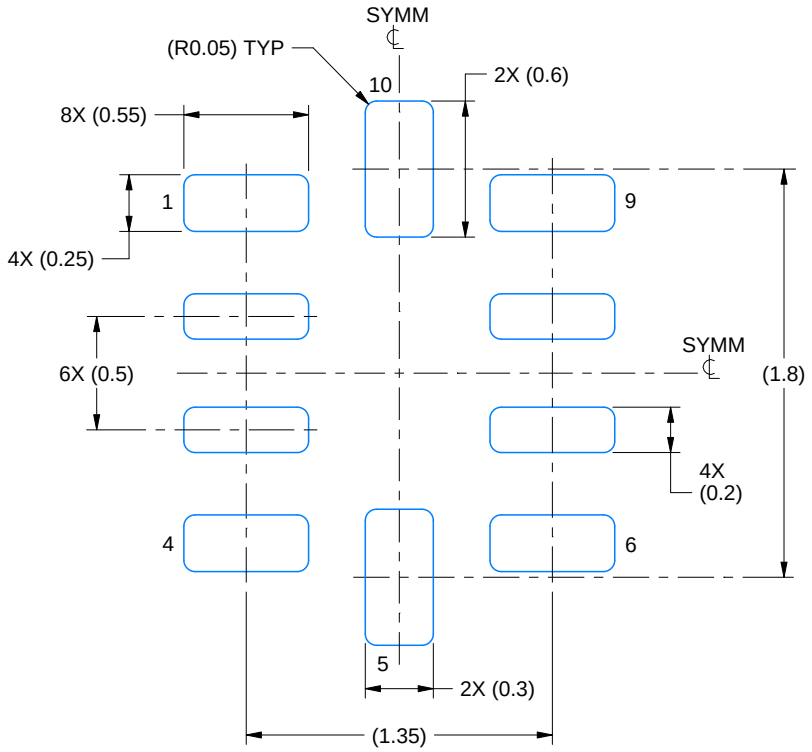
UQFN - 0.6 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

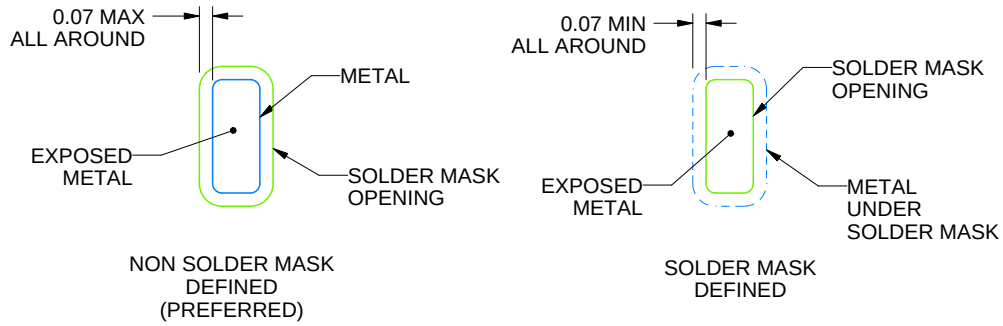


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:30X

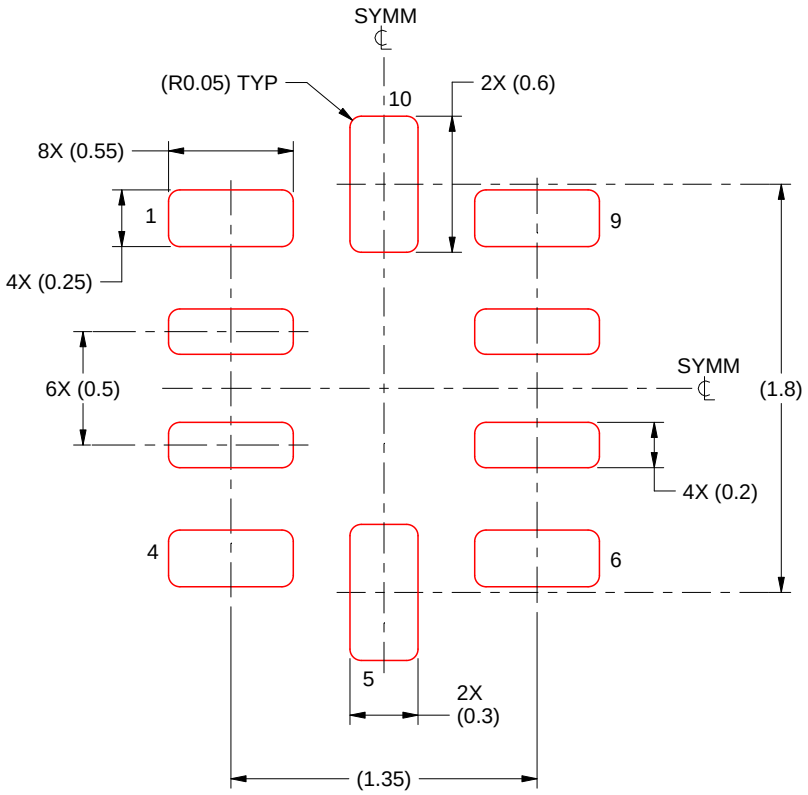


SOLDER MASK DETAILS
NOT TO SCALE

4220307/A 03/2020

NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICKNESS
SCALE: 30X

4220307/A 03/2020

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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